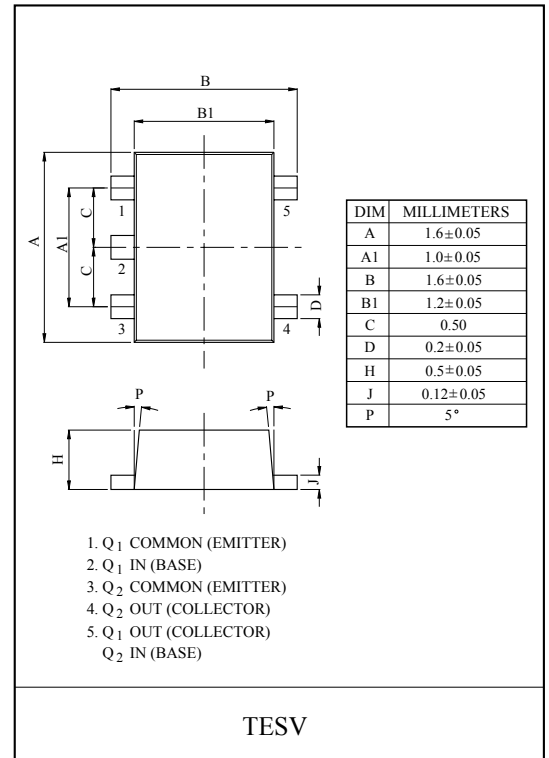
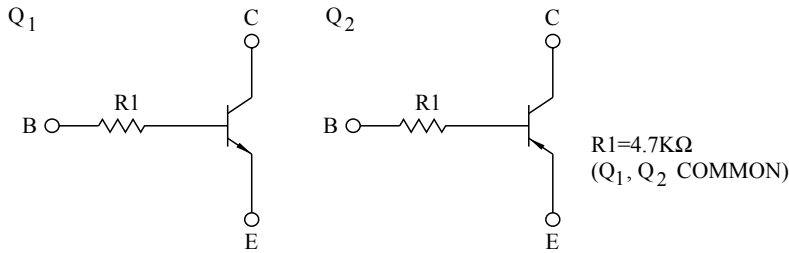


SWITCHING APPLICATION.  
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

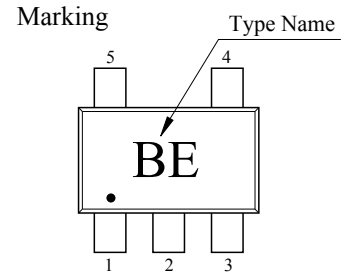
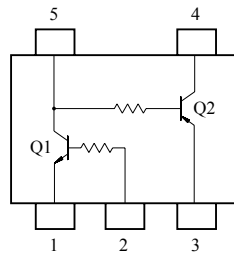
### FEATURES

- Including two devices in TESV.  
(Thin Extreme Super mini type with 5 pin.)
- With Built-in bias resistors.
- Simplify circuit design.
- Reduce a quantity of parts and manufacturing process.

### EQUIVALENT CIRCUIT



### EQUIVALENT CIRCUIT (TOP VIEW)



### Q1 MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	100	mA

### Q2 MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-100	mA

### Q1, Q2 MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Power Dissipation	$P_C^*$	200	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55 ~ 150	°C

\* Total Raing.

# KRX105E

## Q1 ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=50V, I_E=0$	-	-	100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	100	nA
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=1mA$	120	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	-	0.1	0.3	V
Transition Frequency	$f_T^*$	$V_{CE}=10V, I_C=5mA$	-	250	-	MHz
Input Resistor	$R_1$		-	4.7	-	k $\Omega$

Note : \* Characteristic of Transistor Only.

## Q2 ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=-50V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$	-	-	-100	nA
DC Current Gain	$h_{FE}$	$V_{CE}=-5V, I_C=-1mA$	120	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-0.5mA$	-	-0.1	-0.3	V
Transition Frequency	$f_T^*$	$V_{CE}=-10V, I_C=-5mA$	-	250	-	MHz
Input Resistor	$R_1$		-	4.7	-	k $\Omega$

Note : \* Characteristic of Transistor Only.

# KRX105E

